

21st RD50 Workshop (CERN)

Wednesday, 14 November 2012

Defect and Material Characterization (14:00 - 17:50)

-Conveners: Michael Moll

time	[id] title	presenter
14:00	[2] Electronic properties of vacancy aggregates in n-type silicon for particle detectors	Prof. KAMINSKI, Pawel
14:20	[4] Radiation damage in n-type silicon after electron irradiation with energies between 1.5 MeV and 15 MeV	RADU, Roxana
14:40	[25] RADIATION DEFECT TRANSFORMATIONS UNDER ANNEALING OF P-TYPE SILICON	Dr MAKARENKO, Leonid
15:00	[5] Evolution of pulsed current and of carrier lifetime characteristics in Si structures during 25 MeV neutrons irradiation using a spallator type source	Dr GAUBAS, Eugenijus
15:20	[12] The free carrier transport properties in proton and neutron irradiated Si(Ge)	Prof. VAITKUS, Juozas
15:40	Coffee	
16:10	[40] Charge carrier detrapping in irradiated silicon sensors after microsecond laser pulses	GABRYSCH, Markus
16:30	[11] Measurements on 800 MeV proton irradiated diodes (moved to Thursday morning!)	JUNKES, Alexandra
16:50	[16] MOS Capacitor Displacement Damage Dose (DDD) Dosimeter	Dr PALOMO PINTO, Fco.Rogelio
17:10	[47] New proton irradiation facility in Ankara	DEMIRKOZ, Bilge
17:20	[28] Discussion Session: Materials and Defects	MOLL, Michael